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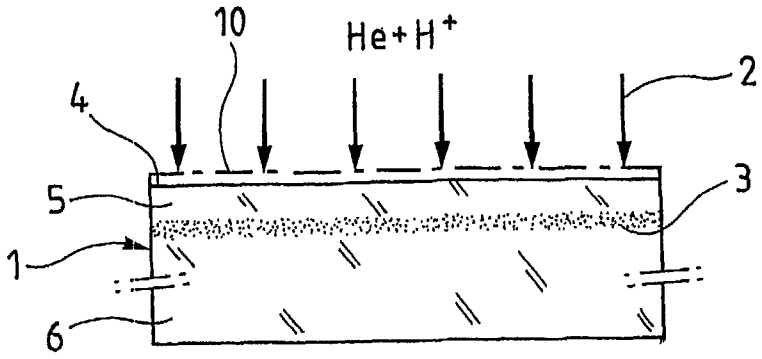
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(54) Title: METHOD OF DETACHING A THIN FILM AT MODERATE TEMPERATURE AFTER CO-IMPLANTATION



(57) Abstract: A method of detaching a thin film from a source substrate comprises the following steps: • implanting ions or gaseous species in the source substrate so as to form therein a buried zone weakened by the presence of defects; • splitting in the weakened zone leading to the detachment of the thin film from the source substrate. Two species are implanted of which one is adapted to form defects and the other is adapted to occupy those defects, the detachment being made at a temperature lower than that for which detachment could be obtained with solely the dose of the first species.

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